

Line Number	Hits	Search Text	DB	Time stamp
1	11872	(resistance or resistivity) with silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:30
2	1131	((resistance or resistivity) with silicide) with electric\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:31
3	705978	electrical adj resistivity of silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:31
4	94	electrical adj resistivity with silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:51
5	4	(aluminum adj silicide) same tantalum same (resistivity or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:36
6	11	(aluminum adj silicide) with (resistivity or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:39
7	4600	tantalum with (resistivity or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:37
8	260	(tantalum with (resistivity or resistance)) with electrical	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:37
9	494	aluminum with silicide with (resistivity or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:39
10	52	(aluminum with silicide with (resistivity or resistance)) with electric\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:39
11	611	electrical adj resistivity with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:51
12	41	electrical adj resistivity adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:52
-	2	6303415.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 15:29
-	2052	tft and crystalliz\$5 and gate and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 16:12
-	704	(tft and crystalliz\$5 and gate and source and drain) and cataly\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 14:40
-	576	((tft and crystalliz\$5 and gate and source and drain) and cataly\$3) and (active adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 14:41
-	270	((tft and crystalliz\$5 and gate and source and drain) and cataly\$3) and (active adj layer)) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 14:46

-	212	(((((tft and crystalliz\$5 and gate and source and drain) and cataly\$3) and (active adj layer)) and getter\$3) and tantalum and nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 14:48
-	5	(((((tft and crystalliz\$5 and gate and source and drain) and cataly\$3) and (active adj layer)) and getter\$3) and tantalum and nickel) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 16:13
-	303	(crystalliz\$5 same silicon same cataly\$3) and getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 16:13
-	24	((crystalliz\$5 same silicon same cataly\$3) and getter\$3) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 11:32
-	2	5550070.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/04 17:10
-	6	("5112764" "5147826" "5275851" "5330935" "5403772" "5426064").PN.	USPAT	2002/12/04 17:45
-	44	5550070.URPN.	USPAT	2002/12/04 18:06
-	168	phosphorus same nickel same getter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 11:31
-	19	(phosphorus same nickel same getter\$3) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 12:01
-	2005	gate with tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 12:00
-	840	(gate with tantalum) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:45
-	31	((gate with tantalum) and @ad<19970610) and crystalliz\$5 and cataly\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:35
-	148	(nickel or ni) with (source or drain) with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:48
-	20	((nickel or ni) with (source or drain) with channel) with concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 13:37
-	74	((nickel or ni) with (source or drain) with channel) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:15
-	149	cataly\$3 with channel with less	USPAT; EPO; JPO; DERWENT	2002/12/06 14:21
-	109	(cataly\$3 with channel with less) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:16
-	47	((cataly\$3 with channel with less) and @ad<19970610) and (nickel or ni)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:16
-	0	(cataly\$3 with channel with less) and "5.times.10.sup.16."	USPAT; EPO; JPO; DERWENT	2002/12/06 14:21

-	3	(ni or nickel) with channel with "5.times.10.sup.16"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:23
-	0	(ni or fe or co or pd or pt or cu or au) with channel with "5.times.10.sup.16"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:25
-	3	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "5.times.10.sup.16"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:26
-	0	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "5.times.10.sup.15"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:26
-	0	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "5.times.10.sup.14"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:26
-	1	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "5.times.10.sup.17"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:26
-	5	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "1.times.10.sup.16"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:31
-	0	(nickel or iron or gold or copper or platinum or palladium or cobalt) with channel with "1.times.10.sup.15"	USPAT; EPO; JPO; DERWENT	2002/12/06 14:45
-	2	6303415.pn.	USPAT; EPO; JPO; DERWENT	2002/12/06 14:45
-	77	(nickel or ni) same (source or drain) same channel same order\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:51
-	16	((nickel or ni) same (source or drain) same channel same order\$1) same concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 14:51
-	2	5550070.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/12/06 17:32
-	370	(interlayer with insulat\$3 with silicon with nitride) and (interlayer with insulat\$3 with (acrylic or polyimide or polyamide or epoxy or epoxies)) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/06 12:32
-	37	((interlayer with insulat\$3 with silicon with nitride) and (interlayer with insulat\$3 with (acrylic or polyimide or polyamide or epoxy or epoxies)) and gate) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/06 12:33
-	2	5550070.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/09/30 20:08
-	2258	silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:16
-	968	(silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:42
-	67	(silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:28
-	17	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:14
-	6	("5112764" "5147826" "5275851" "5330935" "5403772" "5426064").PN.	USPAT	2003/12/08 15:38
-	54	5550070.URPN.	USPAT	2003/12/08 16:13

-	1	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate) and (concentration with nickel with (source or drain) with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:16
-	6	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate) and (concentration same nickel same (source or drain) same channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:32
-	1	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate) and (concentration same (iron or palladium or copper) same (source or drain) same channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:17
-	1	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) same source same drain same gate) and (concentration same iron same (source or drain) same channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:33
-	6	(silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (concentration same (iron or palladium or copper) same (source or drain) same channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:00
-	171	(silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (phosphorus with getter\$3 with nickel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:00
-	2	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (phosphorus with getter\$3 with nickel)) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:05
-	19	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (phosphorus with getter\$3 with nickel)) and @ad<19980610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:11
-	96	(silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (nickel with source with drain with channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:12
-	24	((silicon with (nickel or ni) with (crystallization or crystaliz\$3 or amorphous)) and (nickel with source with drain with channel)) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:12
-	14	("5147826" "5275851" "5481121" "5492843" "5501989" "5529937" "5534716" "5543352" "5550070" "5580792" "5585291" "5612250" "5643826" "5654203").PN.	USPAT	2003/12/08 17:21
-	1370	silicon with iron with (crystallization or crystaliz\$3 or amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:16
-	3	(silicon with iron with (crystallization or crystaliz\$3 or amorphous)) and (concentration same (iron or palladium or copper) same (source or drain) same channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:41
-	6	(concentration with (nickel or iron or palladium or copper) with source with drain with channel) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 18:42
-	30	concentration with (nickel or iron or palladium or copper) with source with drain with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:13

-	19	("5244819" "5534716" "5608232" "5616506" "5639698" "5643826" "5700333" "5736438" "5773309" "5773329" "5821138" "5834071" "5834345" "5869363" "5879977" "5897347" "5923962" "5956579" "6087245").PN.	USPAT	2003/12/08 18:48
-	0	concentration with nickel with source with drain with channel with magnitude	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:16
-	29	concentration with nickel with source with drain with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:14
-	0	nickel with source with drain with channel with magnitude	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:17
-	4	nickel with source with drain with channel with (double or times)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:17
-	2	nickel with source with drain with channel with higher	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:18
-	6	nickel with source with drain with channel with lower	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:25
-	165	nickel with channel with concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:25
-	34	(nickel with channel with concentration) and @ad<19970610	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:26
-	9019939	((nickel with channel with concentration) and @ad<19970610) no (energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 20:26